

Automotive-grade N-channel 650 V, 0.024 Ω typ., 69 A, MDmesh™ V Power MOSFET in a TO-247 package

Datasheet - production data

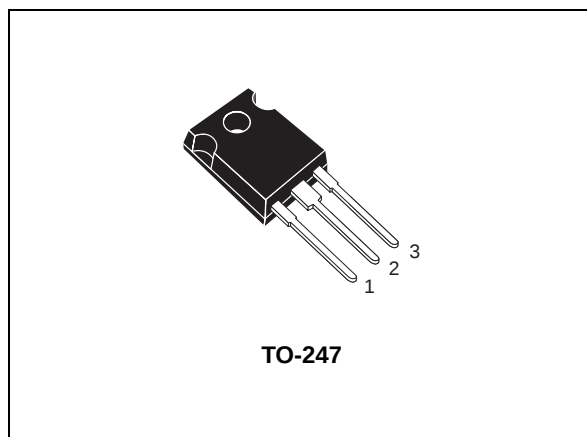
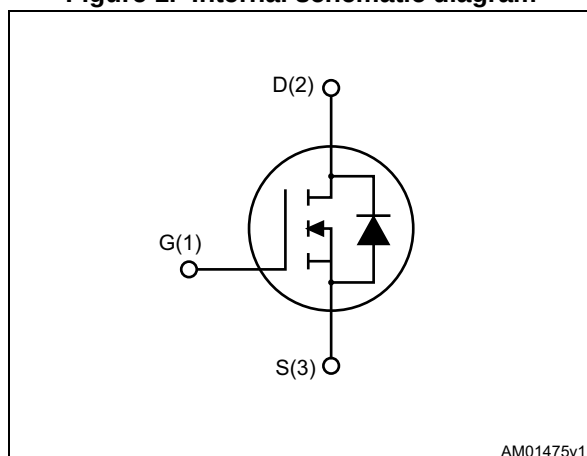


Figure 1. Internal schematic diagram



Features

Order code	$V_{DS} @ T_{jmax.}$	$R_{DS(on)} max.$	I_D
STW78N65M5	710 V	0.032 Ω	69 A

- Designed for automotive applications and AEC-Q101 qualified
- Higher V_{DS} rating
- Higher dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order code	Marking	Package	Packaging
STW78N65M5	78N65M5	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	69	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	41.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	276	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	450	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^{\circ}\text{C}$
T_j	Max. operating junction temperature	150	$^{\circ}\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 69\text{ A}$, $di/dt = 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$

3. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.28	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^{\circ}\text{C}/\text{W}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T_{JMAX})	15	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	2000	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 34.5\text{ A}$		0.024	0.032	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	9000	-	pF
C_{oss}	Output capacitance		-	210	-	pF
C_{rss}	Reverse transfer capacitance		-	9	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	768	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	205	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 34.5\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 16)	-	203	-	nC
Q_{gs}	Gate-source charge		-	50	-	nC
Q_{gd}	Gate-drain charge		-	84	-	nC

1. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
2. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17) (see Figure 20)	-	163	-	ns
$t_{r(V)}$	Voltage rise time		-	14	-	ns
$t_{f(I)}$	Current fall time		-	14	-	ns
$t_{c(off)}$	Crossing time		-	26	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		69	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		276	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 69\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 69\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 17)	-	504		ns
Q_{rr}	Reverse recovery charge		-	13		μC
I_{RRM}	Reverse recovery current		-	49		A
t_{rr}	Reverse recovery time	$I_{SD} = 69\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	635		ns
Q_{rr}	Reverse recovery charge		-	19		μC
I_{RRM}	Reverse recovery current		-	59		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

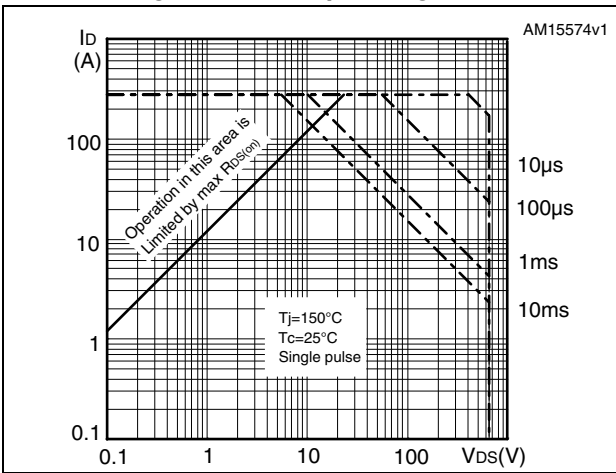


Figure 3. Thermal impedance

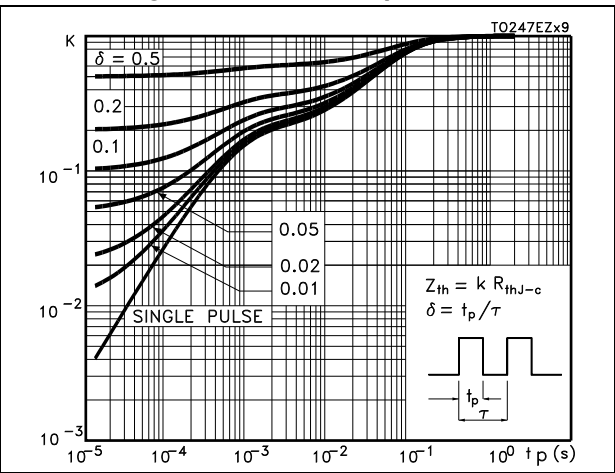


Figure 4. Output characteristics

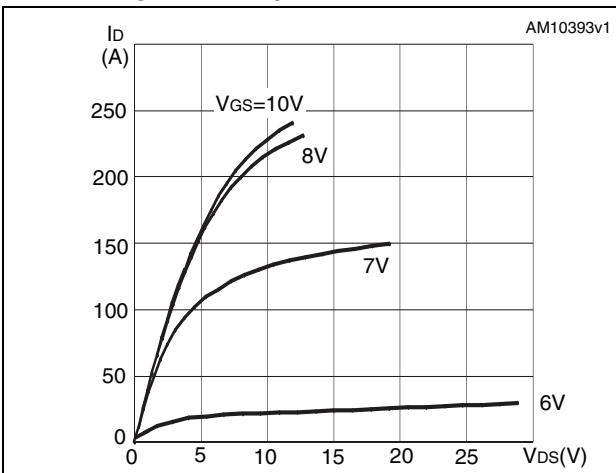


Figure 5. Transfer characteristics

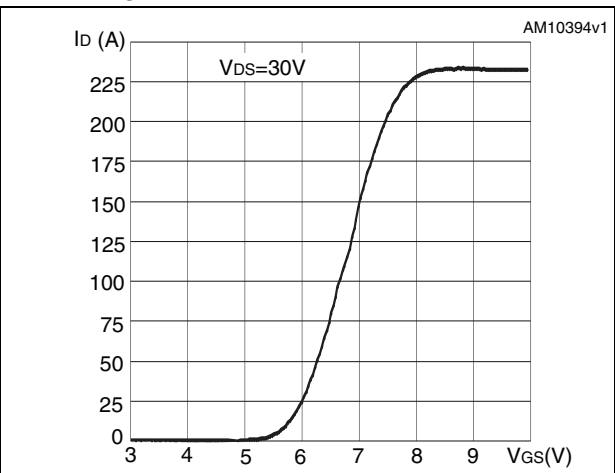


Figure 6. Gate charge vs gate-source voltage

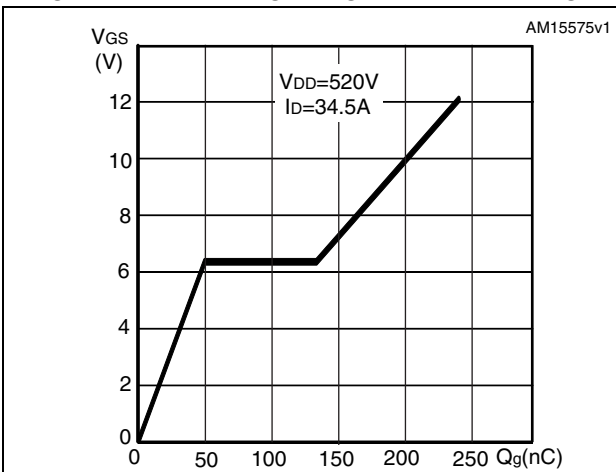


Figure 7. Static drain-source on-resistance

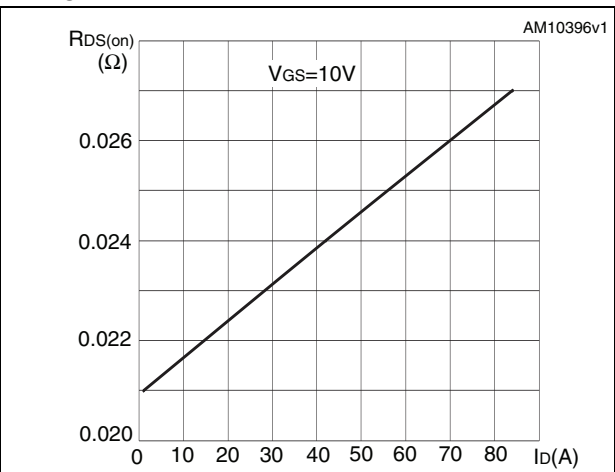


Figure 8. Capacitance variations

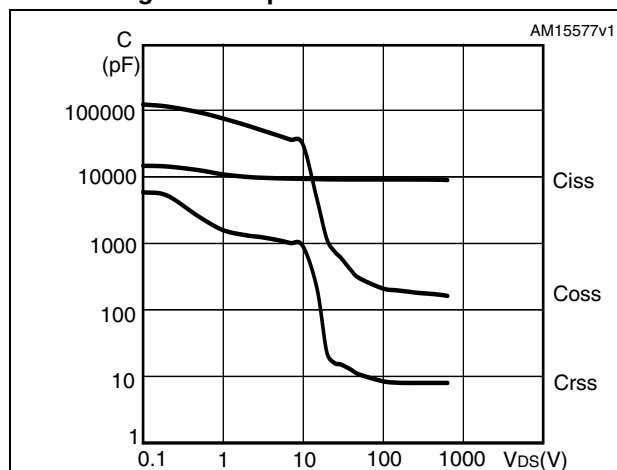


Figure 9. Output capacitance stored energy

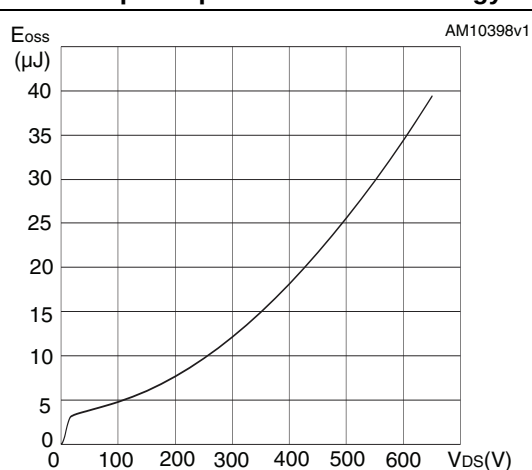


Figure 10. Normalized gate threshold voltage vs temperature

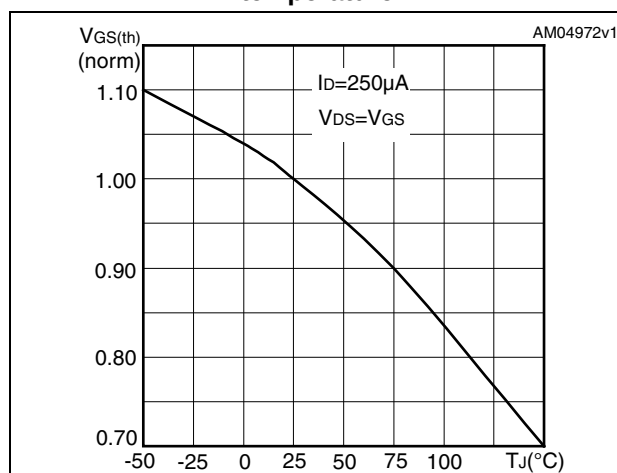


Figure 11. Normalized on-resistance vs temperature

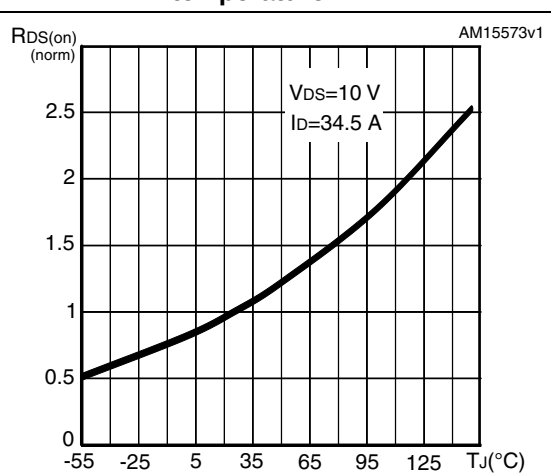


Figure 12. Source-drain diode forward characteristics

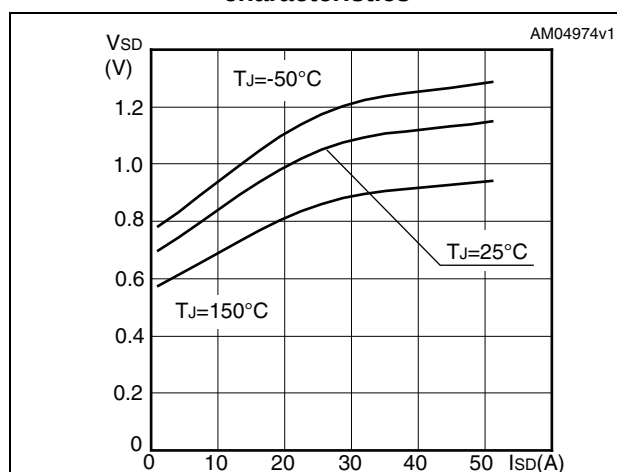
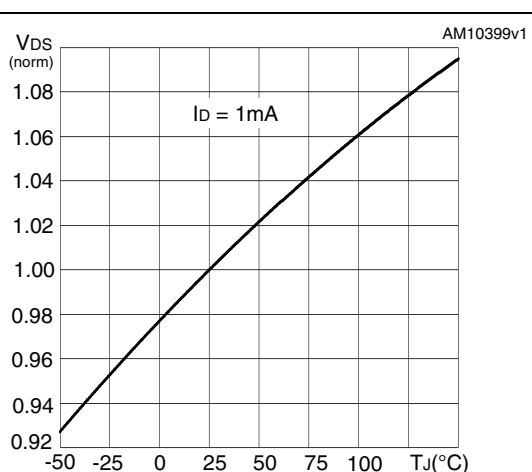
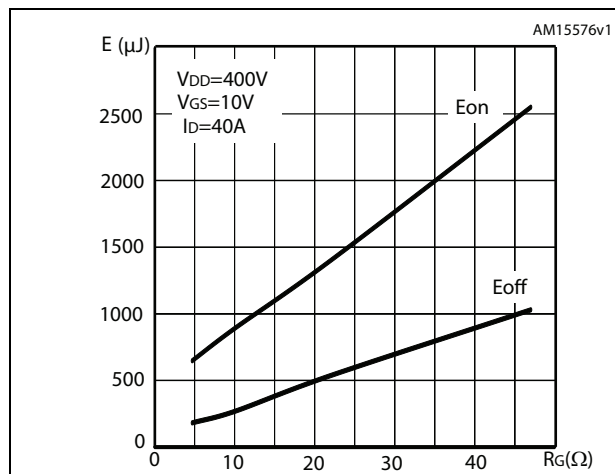
Figure 13. Normalized V_{DS} vs temperature

Figure 14. Switching losses vs gate resistance ⁽¹⁾



1. Eon including reverse recovery of a SiC diode

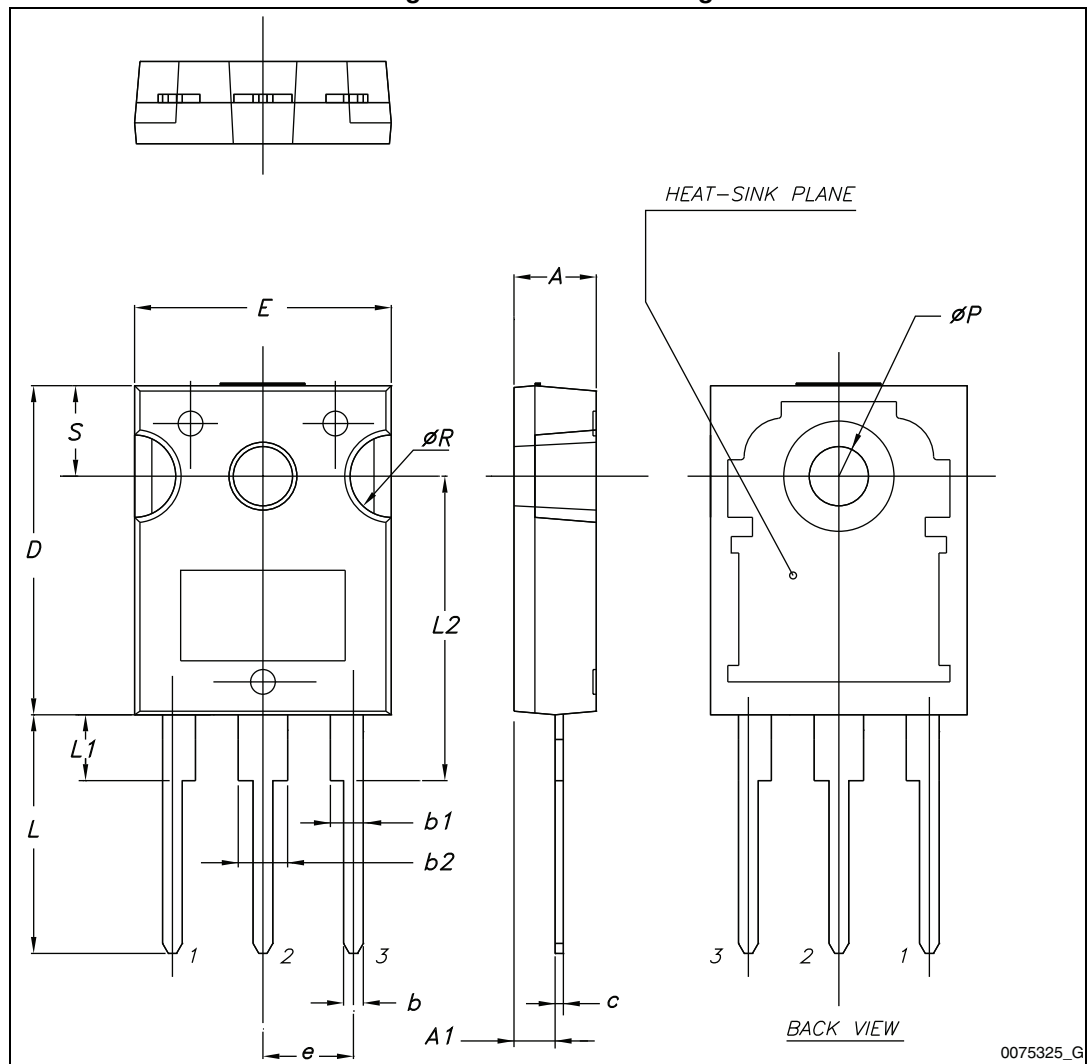
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 21. TO-247 drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
16-Jul-2012	1	First release.
22-Jan-2013	2	Modified: $R_{DS(on)}$ on first page, I_D , I_{DM} on Table 2 , note 2 on Table 2 , typical values on Table 6 , 7 , max and typical values on Table 8 , Figure 2 , 6 , 8 , 9 , 11 and 14
07-Aug-2013	3	– Minor text changes – Modified: Applications in first page – Added: MOSFET dv/dt ruggedness parameter in Table 2 – Added: Table 4: Avalanche characteristics – Modified: Figure 15, 16, 17 and 18
08-Aug-2013	4	– Minor text changes – Modified: Figure 14

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